

Description

The SY405D and SY405T are GaAsP & Gallium Arsenide Phosphide) light emitting diodes which are mounted on lead frames and molded in diffused amber and clear amber plastic, respectively. They are ideally suited for front panel indicator applications.

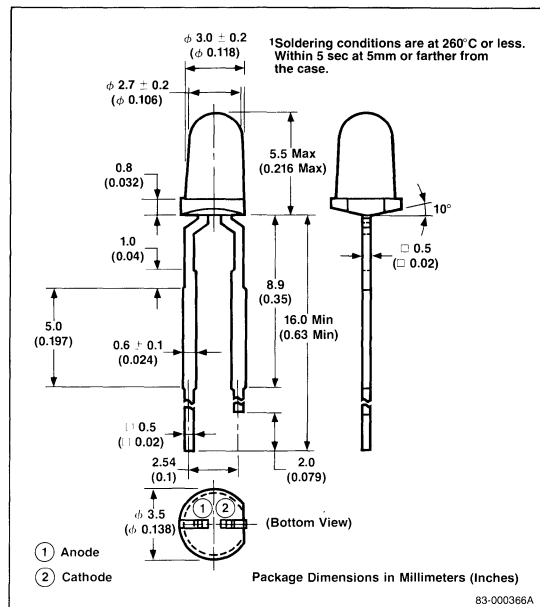
Features

- ☐ Good sensitivity—590nm
- ☐ Long life—solid state reliability
- ☐ Low cost
- ☐ High intensity with low current
- ☐ Versatile mounting on PC board or panel
- ☐ Compatible with integrated circuits
- ☐ Fast switching time

Applications

- ☐ Visual displays
- ☐ Guard systems
- ☐ Radio and stereo equipment indicators
- ☐ Measuring instruments, terminals

Package Dimensions



Absolute Maximum Ratings

 $T_A = +25^{\circ}\text{C}$

Power Dissipation, P_D	100mW
Forward Current, I_F	40mA
Reverse Voltage, V_R	5V
Junction Temperature, T_J	80°C
Storage Temperature, T_{STG}	-30°C to +80°C

Electro-Optical Characteristics

 $T_A = +25^\circ\text{C}$

Parameters	Symbol	Limits			Unit	Test Conditions
		Min	Typ	Max		
Forward Voltage	V_F		2.2	2.5	V	$I_F = 10\text{mA}$
Reverse Current	I_R		0.01	50	μA	$V_R = 4.5$
Capacitance	C_T		60		pF	$V = 0$, $f = 1.0\text{MHz}$
Peak Emission Wavelength	λ_{PEAK}		590		nm	$I_F = 10\text{mA}$
Spectral Line Half Width	$\Delta\lambda$		35		nm	$I_F = 10\text{mA}$
Luminous Intensity	I_{V1}/I_{V21}	1/3	3/5		mcd	$I_F = 10\text{mA}$

Note: 1. I_{V1}/I_{V2} : Luminous intensity of SY 405D/luminous intensity of SY405T.

Typical Characteristics

 $T_A = +25^\circ\text{C}$ 